

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









 V_{RRM} 1200 V **Thyristor**

60 A

1,14 V

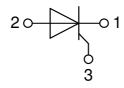
Single Thyristor

Part number

CS60-12io1



Backside: anode



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: PLUS247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;
 the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.



Thyristo	r			 	Ratings	•	i
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM/DSM}	max. non-repetitive reverse/forwa	ard blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
V _{RRM/DRM}	max. repetitive reverse/forward b	<u> </u>	$T_{VJ} = 25^{\circ}C$			1200	V
I _{R/D}	reverse current, drain current	$V_{R/D} = 1200 \text{ V}$	$T_{VJ} = 25^{\circ}C$			200	μΑ
		V _{R/D} = 1200 V	$T_{VJ} = 140^{\circ}C$			10	mA
V_{T}	forward voltage drop	$I_T = 60 \text{ A}$	$T_{VJ} = 25^{\circ}C$			1,18	٧
		I _T = 120 A				1,44	V
		$I_{T} = 60 \text{ A}$	$T_{VJ} = 125$ °C			1,14	٧
		$I_{T} = 120 \text{ A}$				1,46	V
I _{TAV}	average forward current	$T_c = 110$ °C	$T_{VJ} = 140$ °C			60	Α
I _{T(RMS)}	RMS forward current	180° sine				75	Α
V_{T0}	threshold voltage	oss calculation only	$T_{VJ} = 140$ °C			0,82	V
r _T	slope resistance	oss calculation only				5,3	mΩ
R _{thJC}	thermal resistance junction to cas	se				0,32	K/W
\mathbf{R}_{thCH}	thermal resistance case to heatsi	ink			0,15		K/W
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			360	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1,40	kA
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			1,51	kA
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140$ °C			1,19	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			1,29	kA
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			9,80	kA2s
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			9,49	kA2s
		t = 10 ms; (50 Hz), sine	T _{vJ} = 140°C			7,08	kA2s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			6,87	kA2s
C _J	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		74		pF
P _{GM}	max. gate power dissipation	t _P = 30 μs	T _C = 140°C			10	W
		t _P = 300 μs				5	W
P_{GAV}	average gate power dissipation					0,5	W
(di/dt) _{cr}	critical rate of rise of current	$T_{VJ} = 140 ^{\circ}\text{C}; f = 50 \text{Hz}$	epetitive, $I_T = 180 \text{ A}$			150	A/μs
		$t_P = 200 \mu s; di_G/dt = 0.3 A/\mu s;$	•				1
		$I_{G} = 0.3 \text{ A}; V = \frac{2}{3} V_{DRM}$ n	on-repet., $I_{T} = 60 \text{ A}$			500	A/μs
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	T _{v.i} = 140°C			1000	i
, ,,,		R _{GK} = ∞; method 1 (linear volta	ige rise)				! ! !
V _{GT}	gate trigger voltage	V _D = 6 V	T _{v.i} = 25°C			1,5	٧
G1			T _{VJ} = -40°C			1,6	٧
I _{GT}	gate trigger current	$V_D = 6 \text{ V}$	$T_{VJ} = 25^{\circ}C$			100	mA
-01	33	., .	$T_{VJ} = -40$ °C			200	mA
V _{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DBM}$	$T_{VJ} = 140^{\circ}C$			0,2	V
I _{GD}	gate non-trigger current	о ·- · онм	- v _J			10	mA
I _L	latching current	t _o = 10 μs	T _{vJ} = 25°C			450	mA
ıL	.a.o.mg oanon	$I_p = 0.45 \text{ A}; \text{ di}_g/\text{dt} = 0.45 \text{ A}/\mu\text{s}$				730	
<u> </u>	holding current	$V_D = 6 \text{ V } R_{GK} = \infty$	$T_{VJ} = 25$ °C			200	mA
I _H		=	$T_{VJ} = 25^{\circ}C$ $T_{VJ} = 25^{\circ}C$				İ
t _{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$				2	μs
	turn off time	$I_{\rm G} = 0.45 \text{A}; di_{\rm G}/dt = 0.45 \text{A}/\mu s$			450		i !
tq	turn-off time	$V_R = 100 \text{ V}; I_T = 60 \text{ A}; V = \frac{2}{3}$			150		μs
		$di/dt = 10 A/\mu s dv/dt = 20 V$	$t/\mu s t_p = 200 \mu s$				-



Package PLUS247			Ratings			
Symbol	Definition Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current per terminal				70	Α
T _{VJ}	virtual junction temperature				140	°C
T _{op}	operation temperature		-40		125	°C
T _{stg}	storage temperature				140	°C
Weight				6		g
F _c	mounting force with clip		20		120	N
d _{Spp/App}	creepage distance on surface striking distance through a	terminal to terminal	5,5			mm
$d_{Spb/Apb}$	creepage distance on surface striking distance through a	terminal to backside	5,5			mm

Product Marking Logo IIXYS Part No. Assembly Line Zyyww Assembly Code Date Code

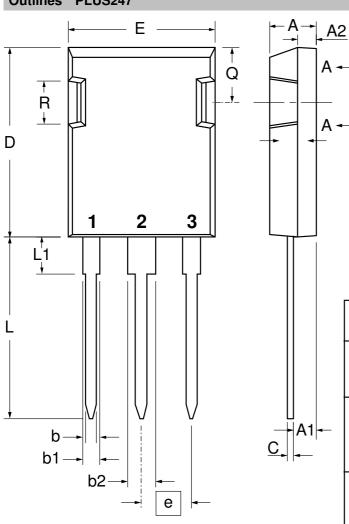
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CS60-12io1	CS60-12io1	Tube	30	503202

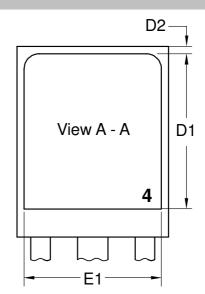
Similar Part	Package	Voltage class
CS60-14io1	PLUS247 (3)	1400
CS60-16io1	PLUS247 (3)	1600

Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 140 ^{\circ}\text{C}$
$I \rightarrow V_0$)— <u>R</u> o	Thyristor		
V _{0 max}	threshold voltage	0,82		V
$R_{0\;max}$	slope resistance *	3		$m\Omega$

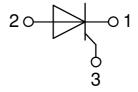


Outlines PLUS247





Sym.	Inches		Millimeter		
	min. max.		min.	max.	
Α	0.190	0.205	4.83	5.21	
A1	0.090	0.100	2.29	2.54	
A2	0.075	0.085	1.91	2.16	
b	0.045	0.055	1.14	1.40	
b1	0.075	0.084	1.91	2.13	
b2	0.115	0.123	2.92	3.12	
С	0.024	0.031	0.61	0.80	
D	0.819	0.840	20.80	21.34	
D1	0.515	-	13.07	-	
D2	0.010	0.053	0.51	1.35	
Е	0.620	0.635	15.75	16.13	
E1	0.530	-	13.45	-	
е	e 0.215 BS		5.45 BSC		
L	0.780	0.800	19.81	20.32	
L1	0.150	0.170	3.81	4.32	
Q	0.220	0.244	5.59	6.20	
R	0.170	0.190	4.32	4.83	





Thyristor

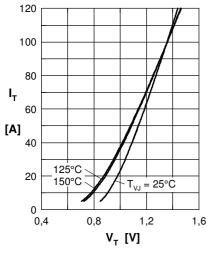


Fig. 1 Forward characteristics

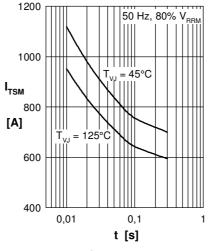


Fig. 2 Surge overload current

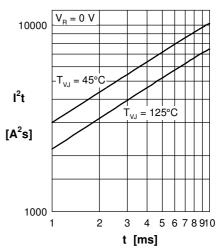


Fig. 3 I²t versus time (1-10 ms)

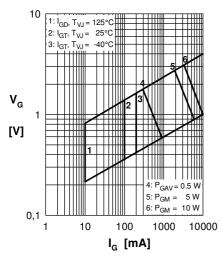


Fig. 4 Gate trigger characteristics

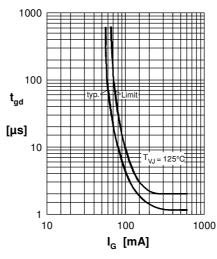


Fig. 5 Gate controlled delay time

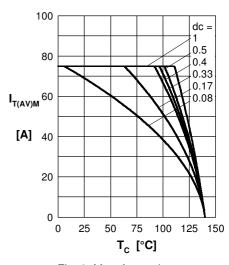


Fig. 6 Max. forward current at case temperature

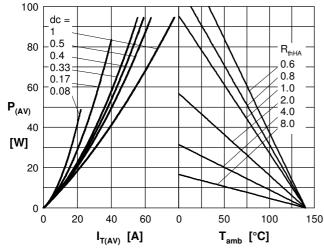


Fig. 7a Power dissipation versus direct output current Fig. 7b and ambient temperature

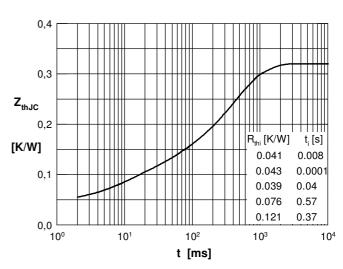


Fig. 8 Transient thermal impedance junction to case